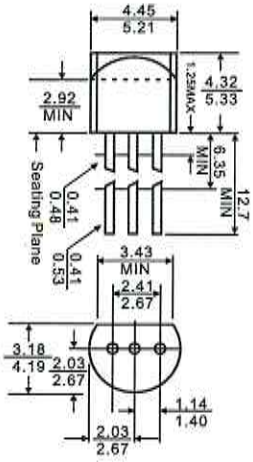
BC556/557/558/559/560

PNP Epitaxial Silicon Transistor

TO-92



1. COLLECTOR
2. BASE
3. EMITTER



Switching and Amplifier

- High Voltage: BC556, V_{CEO}= -65V
- Low Noise: BC559, BC560
- Complement to BC546 ... BC 550

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage		
	: BC556	-80	V
	: BC557/560	-50	V
	: BC558/559	-30	V
V_{CEO}	Collector-Emitter Voltage		
	: BC556	-65	V
	: BC557/560	-45	V
	: BC558/559	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current (DC)	-100	mA
P_C	Collector Power Dissipation	500	mW
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-65 ~ 150	°C

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
I_{CBO}	Collector Cut-off Current	V_{CB}= -30V, I_E=0			-15	nA
h_{FE}	DC Current Gain	V_{CE}= -5V, I_C=2mA	110		800	
V_{CE} (sat)	Collector-Emitter Saturation Voltage	I_C= -10mA, I_B= -0.5mA		-90	-300	mV
		I_C= -100mA, I_B= -5mA		-250	-650	mV
V_{BE} (sat)	Collector-Base Saturation Voltage	I_C= -10mA, I_B= -0.5mA		-700		mV
		I_C= -100mA, I_B= -5mA		-900		mV
V_{BE} (on)	Base-Emitter On Voltage	V_{CE}= -5V, I_C= -2mA	-600	-660	-750	mV
		V_{CE}= -5V, I_C= -10mA			-800	mV
f_T	Current Gain Bandwidth Product	V_{CE}= -5V, I_C= -10mA, f=10MHz		150		MHz
C_{ob}	Output Capacitance	V_{CB}= -10V, I_E=0, f=1MHz			6	pF
NF	Noise Figure : BC556/557/558	V_{CE}= -5V, I_C= -200μA		2	10	dB
	: BC559/560	f=1KHz, R_G=2KΩ		1	4	dB
	: BC559	V_{CE}= -5V, I_C= -200μA		1.2	4	dB
	: BC560	R_G=2KΩ, f=30~15000MHz		1.2	2	dB

h_{FE} Classification

Classification	A	B	C
h_{FE}	110 ~ 220	200 ~ 450	420 ~ 800

Typical Characteristics

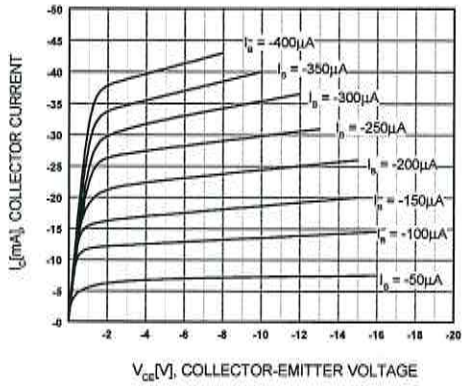


Figure 1. Static Characteristic

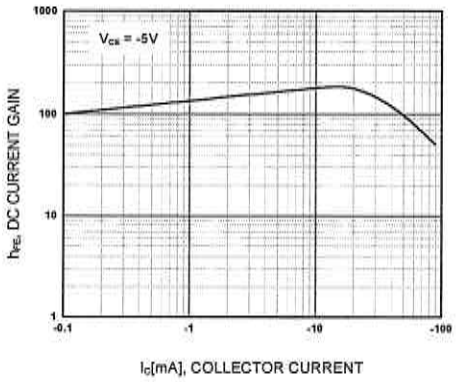


Figure 2. DC current Gain

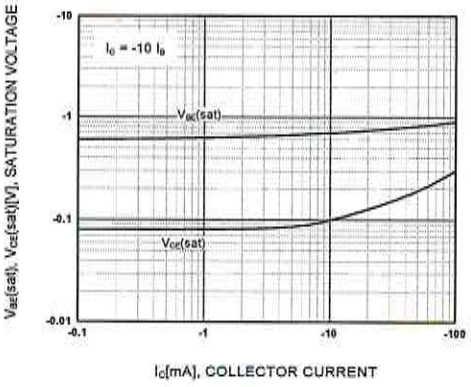


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

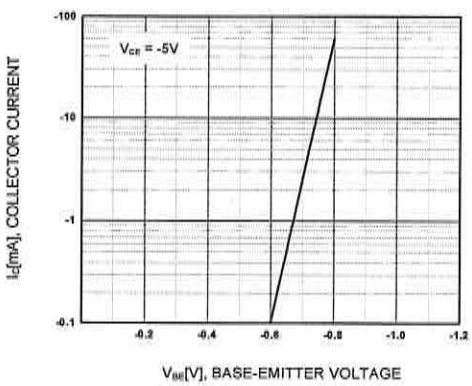


Figure 4. Base-Emitter On Voltage

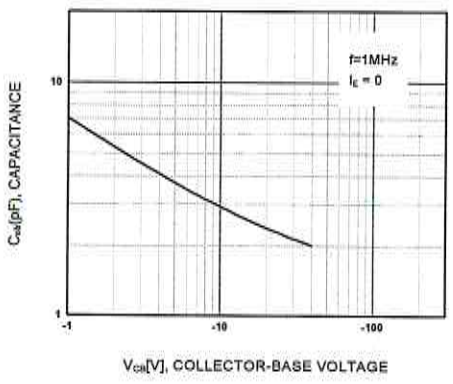


Figure 5. Collector Output Capacitance

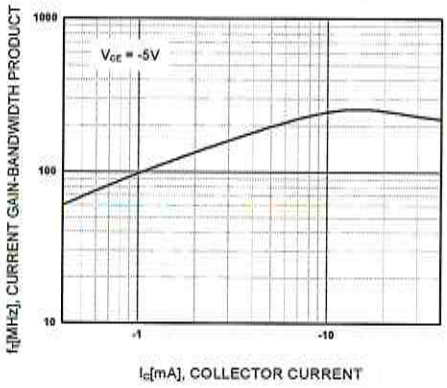


Figure 6. Current Gain Bandwidth Product